



# Schottky Diode

30 V

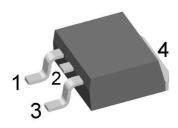
25 A

0.35 V

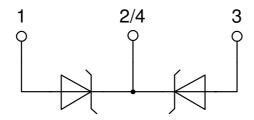
High Performance Schottky Diode Low Loss and Soft Recovery Common Cathode

Part number

#### **DSSK48-003BS**



Backside: cathode



### Features / Advantages:

- Very low Vf
- Extremely low switching losses
- Low Irm values
- Improved thermal behaviour
- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching

### **Applications:**

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Package: TO-263 (D2Pak)

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

#### Terms \_Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact the sales office, which is responsible for you.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact the sales office, which is responsible for you.

Should you intend to use the product in aviation, in health or live endangering or life support applications, please notify. For any such application we urgently recommend

- to perform joint risk and quality assessments;
  the conclusion of quality agreements;
- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747 and per semiconductor unless otherwise specified

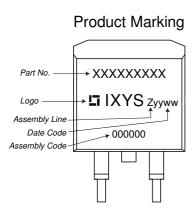
20100209a



Schottky				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V <sub>RSM</sub>	max. non-repetitive reverse block	ing voltage	$T_{VJ} = 25^{\circ}C$			30	V
V <sub>RRM</sub>	max. repetitive reverse blocking v	oltage	$T_{VJ} = 25^{\circ}C$			30	٧
I <sub>R</sub>	reverse current, drain current	$V_R = 30 \text{ V}$	$T_{VJ} = 25^{\circ}C$			20	mA
		$V_R = 30 \text{ V}$	$T_{VJ} = 100$ °C			60	mΑ
V <sub>F</sub>	forward voltage drop	I <sub>F</sub> = 20 A	$T_{VJ} = 25^{\circ}C$			0.44	V
		$I_F = 40 \text{ A}$				0.54	٧
		I <sub>F</sub> = 20 A	T <sub>vJ</sub> = 125°C			0.35	V
		$I_F = 40 \text{ A}$				0.48	٧
I <sub>FAV</sub>	average forward current	T <sub>C</sub> = 130°C	T <sub>vJ</sub> = 150°C			25	Α
		rectangular $d = 0.5$					i 
V <sub>F0</sub>	threshold voltage		T <sub>vJ</sub> = 150°C			0.19	٧
r <sub>F</sub>	slope resistance \( \) for power lo	oss calculation only				6.8	mΩ
R <sub>thJC</sub>	thermal resistance junction to cas	e				1.2	K/W
thCH	thermal resistance case to heatsing	nk			0.25		K/W
P <sub>tot</sub>	total power dissipation		$T_C = 25^{\circ}C$			105	W
I <sub>FSM</sub>	max. forward surge current	$t = 10 \text{ ms}$ ; (50 Hz), sine; $V_R = 0 \text{ V}$	$T_{VJ} = 45^{\circ}C$			300	Α
CJ	junction capacitance	$V_R = 5V f = 1 MHz$	$T_{VJ} = 25^{\circ}C$		1.77		nF



Package TO-263 (D2Pak)			Ratings			
Symbol	Definition	Conditions	mir	. typ.	max.	Unit
RMS	RMS current	per terminal			35	Α
T <sub>vJ</sub>	virtual junction temperature		-(	5	150	°C
T <sub>op</sub>	operation temperature		-[	5	125	°C
T <sub>stg</sub>	storage temperature		-{	5	150	°C
Weight				2	2	g
F <sub>c</sub>	mounting force with clip		2	.0	60	N



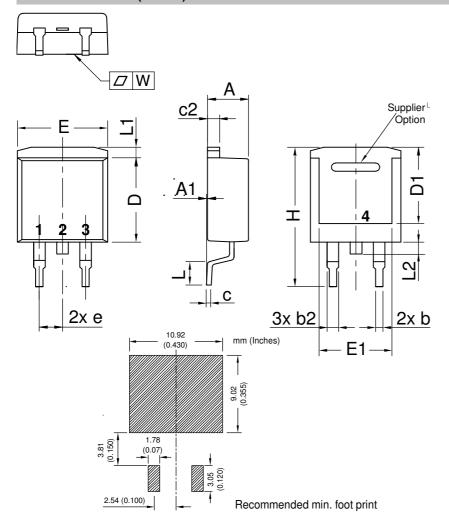
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSSK48-003BS	DSSK48-003BS	Tape & Reel	800	484326
Alternative	DSSK48-003BS-TUB	DSSK48-003BS	Tube	50	484318

Similar Part	Package	Voltage class
DSSK48-003B	TO-220AB (3)	30
DSSK48-0025B	TO-220AB (3)	25

<b>Equivalent Circuits for Simulation</b>			* on die level	$T_{VJ} = 150 ^{\circ}\text{C}$
$I \rightarrow V_0$	)—[R <sub>0</sub> ]-	Schottky		
V <sub>0 max</sub>	threshold voltage	0.19		V
$R_{0 \; max}$	slope resistance *			$m\Omega$

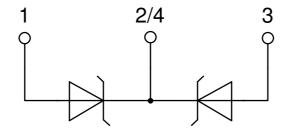


## Outlines TO-263 (D2Pak)



Dim.	Millimeter		Inches		
	min	max	min	max	
Α	4.06	4.83	0.160	0.190	
A1	typ. 0.10		typ. 0	0.004	
A2	2.	41	0.095		
b	0.51	0.99	0.020	0.039	
b2	1.14	1.40	0.045	0.055	
С	0.40	0.74	0.016	0.029	
c2	1.14	1.40	0.045	0.055	
D	8.38	9.40	0.330	0.370	
D1	8.00	8.89	0.315	0.350	
D2	2	.5	0.098		
Е	9.65	10.41	0.380	0.410	
E1	6.22	8.50	0.245	0.335	
е	2,54 BSC		0,100 BSC		
e1	4.28		0.169		
Н	14.61	15.88	0.575	0.625	
L	1.78	2.79	0.070	0.110	
L1	1.02	1.68	0.040	0.066	
W	typ. 0.02	0.040	typ. 0.0008	0.002	

All dimensions conform with and/or within JEDEC standard.





# Schottky

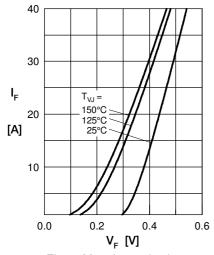


Fig. 1 Max. forward voltage drop characteristics

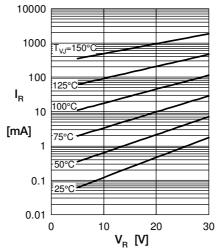


Fig. 2 Typ. reverse current  $I_{\rm R}$  vs. reverse voltage  $V_{\rm R}$ 

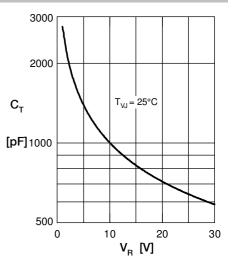


Fig. 3 Typ. junction capacitance  $C_T$  vs. reverse voltage  $V_R$ 

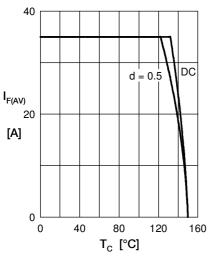


Fig. 4 Average forward current  $I_{F(AV)}$  vs. case temp.  $T_{C}$ 

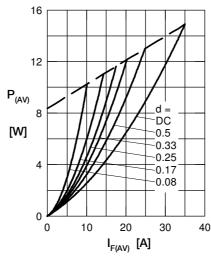


Fig. 5 Forward power loss characteristics

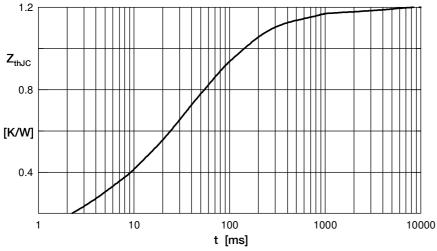


Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode